ABSTRACT OF THE DISCLOSURE

It is an object of the invention to provide a backing plate used for the sputtering apparatus and a sputtering method which can improve film deposition rate and film quality without increasing the size of the target with respect to the substrate. High sputtering power is applied to a target portion opposite to a location where a thin film is formed on a surface of a substrate, thereby a thin film having even film thickness and film quality can be formed without increasing the size of the target. Further, a cooling medium flow passage can eliminate temperature unevenness caused by different sputtering powers to be applied to a target surface. The problem caused by the temperature rise can be solved and the film deposition speed can be enhanced by increasing the sputtering power which can be applied to the target. Consequently, it is possible to improve productivity of the substrate.